Amendments to the Claims

Claims 1-54 are cancelled.

55. (Currently amended) A method of forming a capacitor comprising:

providing a substrate having a node location disposed between a first conductive line and a second conductive line;

forming a contact structure in electrical communication with the node location, the contact structure extending laterally over at least a portion of each of the conductive lines;

forming an insulative material over the contact structure; and

forming capacitor containers in electrical communication with the node location, the capacitor containers consisting of a first container disposed at least partially over only the first ~~first~~ conductive line and a second container disposed at least partially over only the second conductive line, the first container being spaced from the second container by a lateral distance, the insulating material being disposed between the first and second containers and extending the entirety of the lateral distance from the first container to the second container.

56. (Currently amended) The method of claim 55 wherein the forming the capacitor containers ~~capacitors~~ comprises:

forming a masking layer over the substrate, ~~substrate and~~ over the conductive lines, and over the insulative material;

forming a first opening within the masking layer over the first conductive line;

forming a second opening within the masking layer over the second conductive line; and

depositing a conductive material within the first and second openings, the conductive material being in direct physical contact with the contact structure.

57. (Previously presented) The method of claim 56 wherein the conductive material comprises polysilicon.

58. (Previously presented) The method of claim 55 further comprising:

lining the capacitor containers with a dielectric material; and

forming a capacitor electrode layer over the dielectric material and within the first and second containers.

59. (Previously presented) A method of forming a capacitor structure comprising:

providing a substrate having a substrate node location;

forming a contact structure in electrical communication with the substrate node location, the contact structure being disposed between two conductive lines, extending elevationally above and laterally outward over and contacting an uppermost surface of each of the two conductive lines;

forming a first container having a continuous conductive layer defining a first interior area, the conductive layer being joined with the contact structure, the first container being disposed at least partially over one of the two conductive lines;

forming a second container having a continuous conductive layer defining a second interior area, the conductive layer being joined with the contact structure, the first and second interior areas being spaced apart from one another in a non-overlapping relationship; and

forming a dielectric layer and a conductive capacitor electrode layer disposed operably proximate the first container the second container and portions of the contact structure.

60. (Previously presented) The method of claim 59, wherein the containers are elongate and extend along generally parallel central axes.

61. (Previously presented) The method of claim 59, wherein the capacitor containers are laterally separated by a dielectric region, at least one of the containers being elongate and generally tubular in shape.

62. (Currently amended) A method of forming DRAM circuitry comprising:

providing a substrate having first and second spaced apart node locations;

forming a first storage capacitor in electrical communication with the first node location and comprising cylinder structures ~~capacitor containers~~ consisting of first and second cylinders ~~containers~~, the first cylinder ~~container~~ being at least partially disposed over a first conductive line, the second cylinder ~~container~~ being disposed at least partially over a second conductive line;

forming a second storage capacitor in electrical communication with the second node location and comprising capacitor cylinders ~~containers~~ consisting of third and fourth cylinders ~~containers~~ , the third cylinder ~~container~~ being disposed at least partially over a third conductive line, the fourth cylinder ~~container~~ being at least partially disposed over a fourth conductive line;

lining the first, second third and fourth cylinders ~~containers~~ with a dielectric layer; and

depositing a conductive capacitor electrode layer over the dielectric layer and within the cylinders ~~containers~~.

63. (Currently amended) The method of claim 62, wherein the cylinders ~~containers~~ are generally elongate.

64. (Currently amended) The method of claim 62, wherein the cylinders ~~containers~~ are generally elongate and extend along respective central axes at least two of which being generally parallel.

65. (Currently amended) The method of claim 62, wherein the cylinders ~~containers~~ are generally elongate and extend along respective central axes which are generally parallel with one another.

66. (Currently amended) The method of claim 62, wherein the cylinders ~~containers~~ are generally elongate and extend along respective central axes, and wherein

each cylinder ~~container~~ comprises a respective portion which has a generally circular transverse cross-section.

67. (Currently amended) The method of claim 62, wherein each cylinder ~~container~~ has a volume which is substantially equivalent relative to the each other.